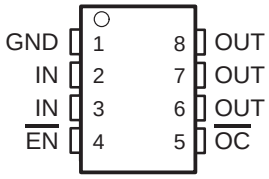
features

- 135-mΩ -Maximum (5-V Input) High-Side MOSFET Switch
- 250 mA Continuous Current
- Short-Circuit and Thermal Protection With Overcurrent Logic Output
- Operating Range . . . 2.7-V to 5.5-V
- Logic-Level Enable Input
- 2.5-ms Typical Rise Time
- Undervoltage Lockout
- 10 μA Maximum Standby Supply Current
- Bidirectional Switch
- Available in 8-pin SOIC and PDIP Packages
- Ambient Temperature Range, –40°C to 85°C
- 2-kV Human-Body-Model, 200-V Machine-Model ESD Protection

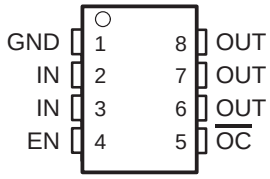
typical applications

- Notebook, Desktop and Palmtop PCs
- Monitors, Keyboards, Scanners, and Printers
- Digital Cameras, Phones, and PBXs
- Hot-Insertion Applications

TPS2045
D OR P PACKAGE
(TOP VIEW)



TPS2055
D OR P PACKAGE
(TOP VIEW)



description

The TPS2045 and TPS2055 power-distribution switches are intended for applications where heavy capacitive loads and short circuits are likely. Each of these 135-mΩ N-channel MOSFET high-side power switches is controlled by a logic enable compatible with 5-V and 3-V logic. Gate drive is provided by an internal charge pump that controls the power-switch rise times and fall times to minimize current surges during switching. The charge pump requires no external components and allows operation from supplies as low as 2.7 V.

When the output load exceeds the current-limit threshold or a short is present, the TPS2045 and TPS2055 limit the output current to a safe level by switching into a constant-current mode, pulling the overcurrent ($\overline{OC}$) logic output low. When continuous heavy overloads and short circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch in overcurrent to prevent damage. Recovery from a thermal shutdown is automatic once the device has cooled sufficiently. Internal circuitry ensures the switch remains off until valid input voltage is present.

The TPS2045 and TPS2055 are designed to limit at 0.44-A load. These power-distribution switches, available in 8-pin small-outline integrated circuit (SOIC) and 8-pin plastic dual-in-line packages (PDIP), operate over an ambient temperature range of –40°C to 85°C.

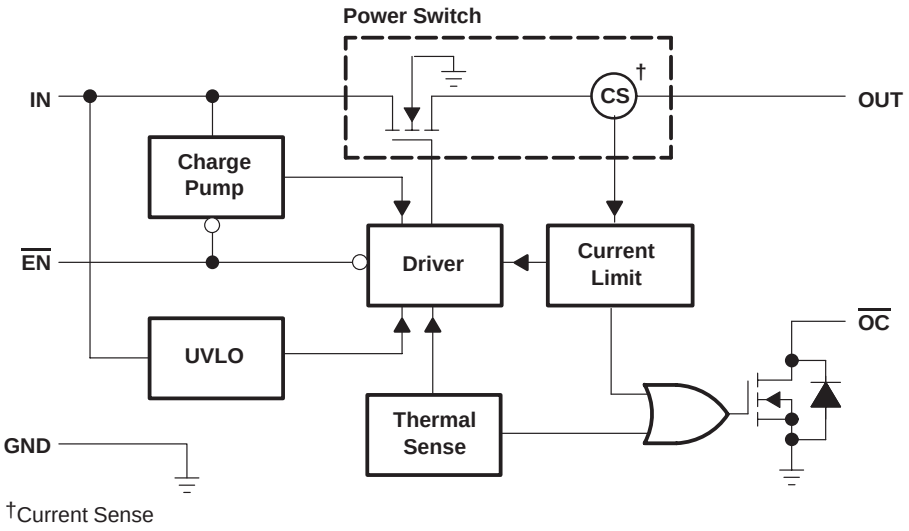
AVAILABLE OPTIONS

T_A	ENABLE	RECOMMENDED MAXIMUM CONTINUOUS LOAD CURRENT (A)	TYPICAL SHORT-CIRCUIT CURRENT LIMIT AT 25°C (A)	PACKAGED DEVICES	
				SOIC (D)†	PDIP (P)
–40°C to 85°C	Active low	0.25	0.44	TPS2045D	TPS2045P
–40°C to 85°C	Active high	0.25	0.44	TPS2055D	TPS2055P

† The D package is available taped and reeled. Add an R suffix to device type (e.g., TPS2045DR)

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

TPS2045 functional block diagram



Terminal Functions

TERMINAL			I/O	DESCRIPTION
NAME	NO. D OR P			
	TPS2045	TPS2055		
$\overline{EN}$	4	–	I	Enable input. Logic low turns on power switch.
EN	–	4	I	Enable input. Logic high turns on power switch.
GND	1	1	I	Ground
IN	2, 3	2, 3	I	Input voltage
$\overline{OC}$	5	5	O	Over current. Logic output active low
OUT	6, 7, 8	6, 7, 8	O	Power-switch output

detailed description

power switch

The power switch is an N-channel MOSFET with a maximum on-state resistance of 135 mΩ ($V_{I(IN)}$ = 5 V). Configured as a high-side switch, the power switch prevents current flow from OUT to IN and IN to OUT when disabled. The power switch can supply a minimum of 250 mA per switch.

charge pump

An internal charge pump supplies power to the driver circuit and provides the necessary voltage to pull the gate of the MOSFET above the source. The charge pump operates from input voltages as low as 2.7 V and requires very little supply current.

driver

The driver controls the gate voltage of the power switch. To limit large current surges and reduce the associated electromagnetic interference (EMI) produced, the driver incorporates circuitry that controls the rise times and fall times of the output voltage. The rise and fall times are typically in the 2-ms to 4-ms range.

enable ($\overline{EN}$ or EN)

The logic enable disables the power switch and the bias for the charge pump, driver, and other circuitry to reduce the supply current to less than 10 μA when a logic high is present on $\overline{EN}$ (TPS2045) or a logic low is present on EN (TPS2055). A logic zero input on $\overline{EN}$ or a logic high on EN restores bias to the drive and control circuits and turns the power on. The enable input is compatible with both TTL and CMOS logic levels.

overcurrent ($\overline{OC}$)

The $\overline{OC}$ open-drain output is asserted (active low) when an overcurrent or overtemperature condition is encountered. The output will remain asserted until the overcurrent or overtemperature condition is removed.

current sense

A sense FET monitors the current supplied to the load. The sense FET measures current more efficiently than conventional resistance methods. When an overload or short circuit is encountered, the current-sense circuitry sends a control signal to the driver. The driver in turn reduces the gate voltage and drives the power FET into its saturation region, which switches the output into a constant current mode and holds the current constant while varying the voltage on the load.

thermal sense

An internal thermal-sense circuit shuts off the power switch when the junction temperature rises to approximately 140°C. Hysteresis is built into the thermal sense circuit. After the device has cooled approximately 20°C, the switch turns back on. The switch continues to cycle off and on until the fault is removed.

undervoltage lockout

A voltage sense circuit monitors the input voltage. When the input voltage is below approximately 2 V, a control signal turns off the power switch.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Input voltage range, $V_{I(IN)}$ (see Note 1) . . . . . –0.3 V to 6 V
Output voltage range, $V_{O(OUT)}$ (see Note 1) . . . . . –0.3 V to $V_{I(IN)}$ + 0.3 V
Input voltage range, $V_{I(\overline{EN})}$ or $V_{I(EN)}$ . . . . . –0.3 V to 6 V
Continuous output current, $I_{O(OUT)}$ . . . . . internally limited
Continuous total power dissipation . . . . . See Dissipation Rating Table
Operating virtual junction temperature range, T_J . . . . . –40°C to 125°C
Storage temperature range, T_{stg} . . . . . –65°C to 150°C
Lead temperature soldering 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C
Electrostatic discharge (ESD) protection: Human body model MIL-STD-883C . . . . . 2 kV
Machine model . . . . . 0.2 kV

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltages are with respect to GND.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING
D	725 mW	5.8 mW/°C	464 mW	377 mW
P	1175 mW	9.4 mW/°C	752 mW	611 mW

recommended operating conditions

	TPS2045		TPS2055		UNIT
	MIN	MAX	MIN	MAX	
Input voltage, $V_{I(IN)}$	2.7	5.5	2.7	5.5	V
Input voltage, $V_{I(\overline{EN})}$ or $V_{I(EN)}$	0	5.5	0	5.5	V
Continuous output current, $I_{O(OUT)}$	0	250	0	250	mA
Operating virtual junction temperature, T_J	–40	125	–40	125	°C

electrical characteristics over recommended operating junction temperature range, $V_{I(IN)}$= 5.5 V, I_O = rated current, $V_{I(\overline{EN})}$= 0 V, $V_{I(EN)}$ = Hi (unless otherwise noted)

power switch

PARAMETER		TEST CONDITIONS†	TPS2045			TPS2055			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
$r_{DS(on)}$	Static drain-source on-state resistance, 5-V operation	$V_{I(IN)}$ = 5 V, I_O = 0.25 A, T_J = 25°C		80	95		80	95	mΩ
		$V_{I(IN)}$ = 5 V, I_O = 0.25 A, T_J = 85°C		90	120		90	120	
		$V_{I(IN)}$ = 5 V, I_O = 0.25 A, T_J = 125°C		100	135		100	135	
	Static drain-source on-state resistance, 3.3-V operation	$V_{I(IN)}$ = 3.3 V, I_O = 0.25 A, T_J = 25°C		85	105		85	105	
		$V_{I(IN)}$ = 3.3 V, I_O = 0.25 A, T_J = 85°C		100	135		100	135	
		$V_{I(IN)}$ = 3.3 V, I_O = 0.25 A, T_J = 125°C		115	150		115	150	
t_r	Rise time, output	$V_{I(IN)}$ = 5.5 V, C_L = 1 µF, R_L = 20 Ω, T_J = 25°C		2.5			2.5		ms
		$V_{I(IN)}$ = 2.7 V, C_L = 1 µF, R_L = 20 Ω, T_J = 25°C		3			3		
t_f	Fall time, output	$V_{I(IN)}$ = 5.5 V, C_L = 1 µF, R_L = 20 Ω, T_J = 25°C		4.4			4.4		ms
		$V_{I(IN)}$ = 2.7 V, C_L = 1 µF, R_L = 20 Ω, T_J = 25°C		2.5			2.5		

† Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

enable input $\overline{EN}$ or EN

PARAMETER			TEST CONDITIONS	TPS2045			TPS2055			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
V_{IH}	High-level input voltage		2.7 V ≤ $V_{I(IN)}$ ≤ 5.5 V	2			2			V
V_{IL}	Low-level input voltage		4.5 V ≤ $V_{I(IN)}$ ≤ 5.5 V			0.8			0.8	V
			2.7 V ≤ $V_{I(IN)}$ ≤ 4.5 V			0.4			0.4	
I_I	Input current	TPS2045	$V_{I(\overline{EN})}$ = 0 V or $V_{I(EN)}$ = $V_{I(IN)}$	–0.5		0.5				µA
		TPS2055	$V_{I(\overline{EN})}$ = $V_{I(IN)}$ or $V_{I(EN)}$ = 0 V				–0.5		0.5	
t_{on}	Turnon time		C_L = 100 µF, R_L = 20 Ω			20			20	ms
t_{off}	Turnoff time		C_L = 100 µF, R_L = 20 Ω			40			40	

current limit

PARAMETER		TEST CONDITIONS†	TPS2045			TPS2055			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
I_{OS}	Short-circuit output current	$V_{I(IN)}$ = 5 V, OUT connected to GND, Device enabled into short circuit	0.345	0.44	0.525	0.345	0.44	0.525	A

† Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

electrical characteristics over recommended operating junction temperature range, $V_{I(IN)}$= 5.5 V, I_O = rated current, $V_{I(\overline{EN})}$ = 0 V, $V_{I(EN)}$ = Hi (unless otherwise noted) (continued)

supply current

PARAMETER	TEST CONDITIONS				TPS2045			TPS2055			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
Supply current, low-level output	No Load on OUT	$V_{I(\overline{EN})} = V_{I(IN)}$	T_J = 25°C	TPS2045		0.015	1				µA
			–40°C ≤ T_J ≤ 125°C				10				
		$V_{I(EN)}$ = 0 V	T_J = 25°C	TPS2055					0.015	1	
			–40°C ≤ T_J ≤ 125°C							10	
Supply current, high-level output	No Load on OUT	$V_{I(\overline{EN})}$ = 0 V	T_J = 25°C	TPS2045		80	100				µA
			–40°C ≤ T_J ≤ 125°C			100					
		$V_{I(EN)} = V_{I(IN)}$	T_J = 25°C	TPS2055					80	100	
			–40°C ≤ T_J ≤ 125°C						100		
Leakage current	OUT connected to ground	$V_{I(\overline{EN})} = V_{I(IN)}$	–40°C ≤ T_J ≤ 125°C	TPS2045		100					µA
		$V_{I(EN)}$ = 0 V	–40°C ≤ T_J ≤ 125°C	TPS2055					100		
Reverse leakage current	IN = high impedance	$V_{I(\overline{EN})}$ = 0 V	T_J = 25°C	TPS2045		0.3					µA
		$V_{I(EN)}$ = Hi		TPS2055					0.3		

undervoltage lockout

PARAMETER	TEST CONDITIONS	TPS2045			TPS2055			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
Low-level input voltage		2		2.5	2		2.5	V
Hysteresis	T_J = 25°C		100			100		mV

overcurrent $\overline{OC}$

PARAMETER	TEST CONDITIONS	TPS2045			TPS2055			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
Sink current†	V_O = 5 V			10			10	mA
Output low voltage	I_O = 5 V, $V_{OL(\overline{OC})}$			0.5			0.5	V
Off-state current†	V_O = 5 V, V_O = 3.3 V			1			1	µA

† Specified by design, not production tested.

PARAMETER MEASUREMENT INFORMATION

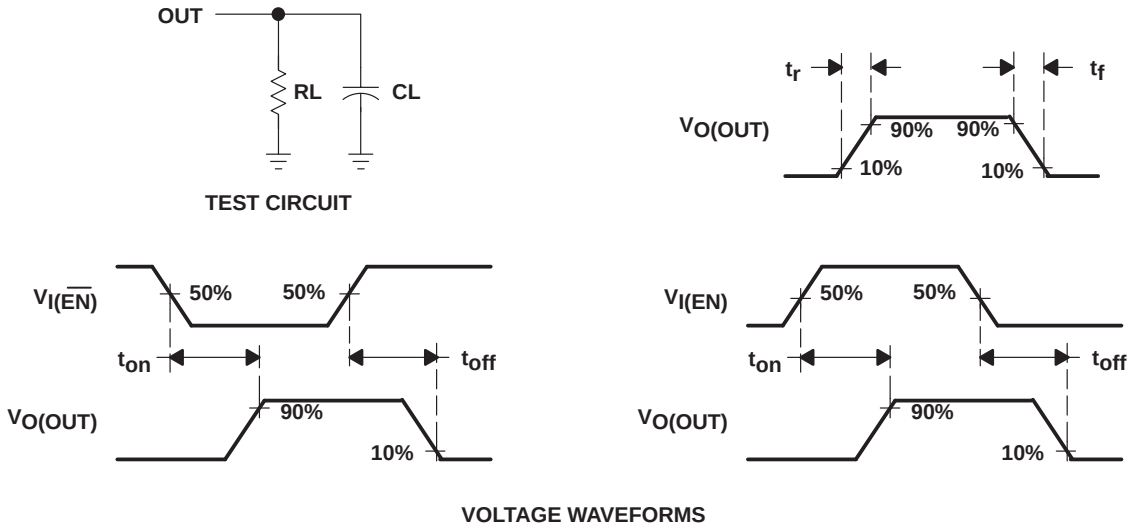


Figure 1. Test Circuit and Voltage Waveforms

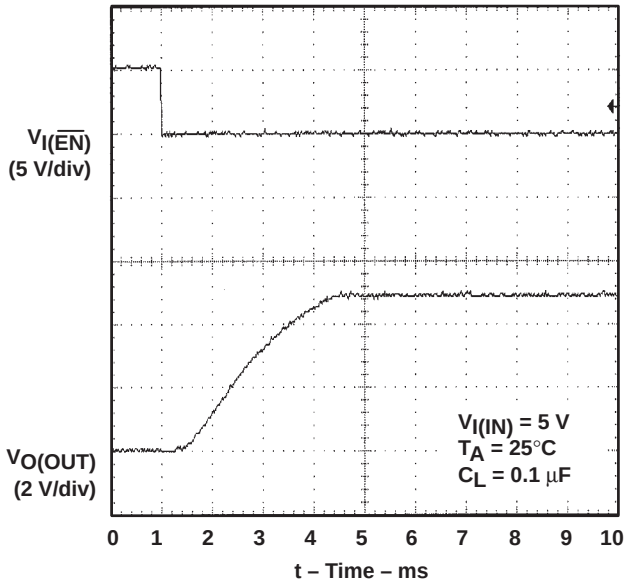


Figure 2. Turnon Delay and Rise Time with 0.1-μF Load

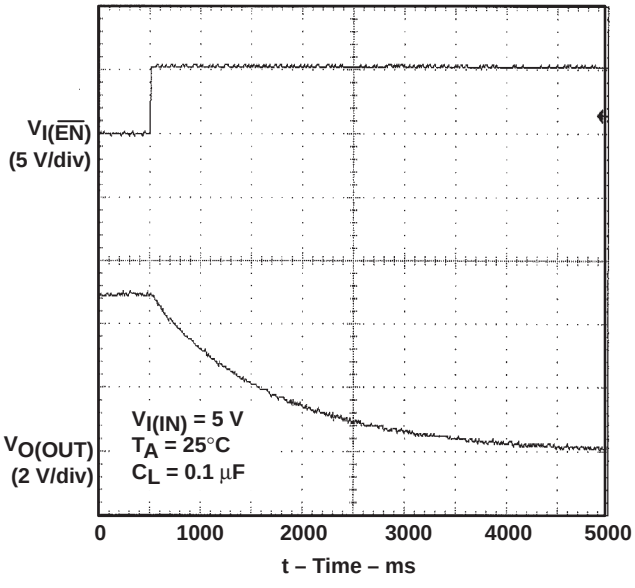


Figure 3. Turnoff Delay and Fall Time with 0.1-μF Load

PARAMETER MEASUREMENT INFORMATION

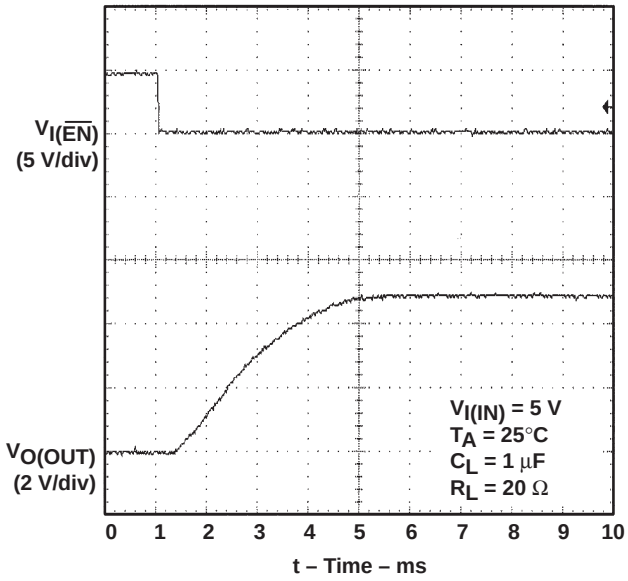


Figure 4. Turnon Delay and Rise Time with 1-μF Load

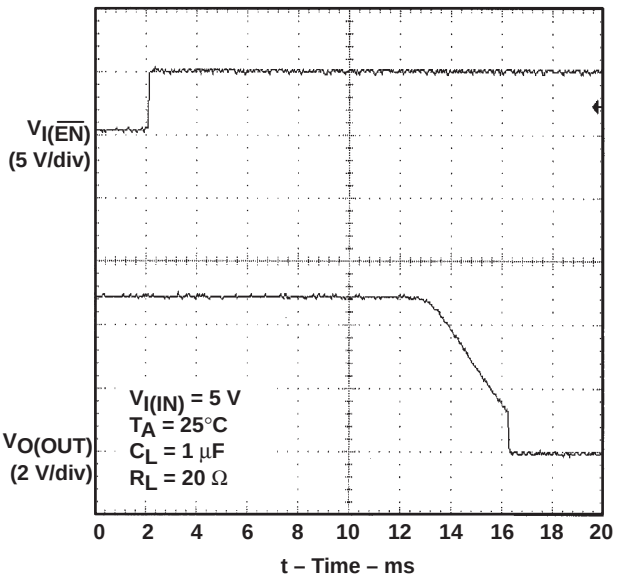


Figure 5. Turnoff Delay and Fall Time with 1-μF Load

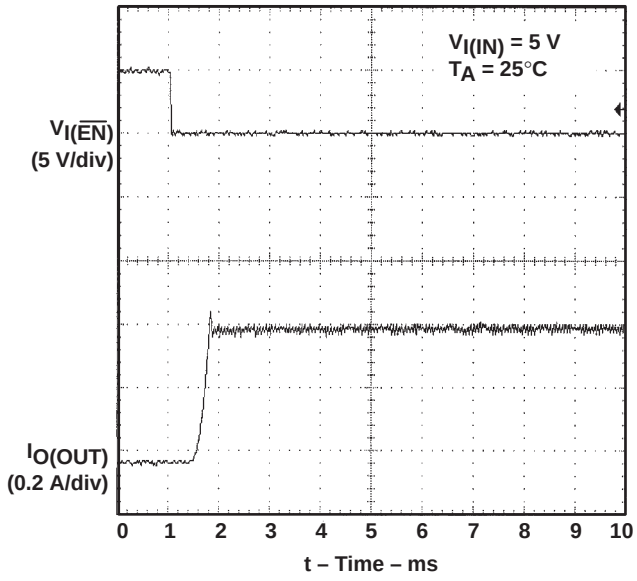


Figure 6. TPS2045, Short-Circuit Current, Device Enabled into Short

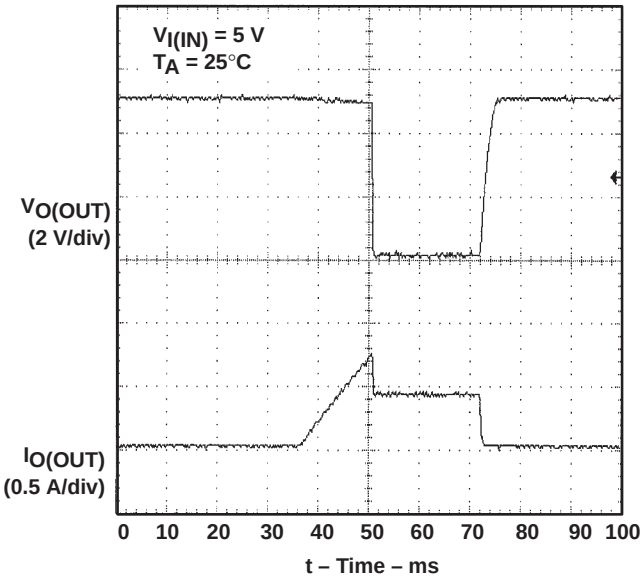


Figure 7. TPS2045, Threshold Trip Current with Ramped Load on Enabled Device

PARAMETER MEASUREMENT INFORMATION

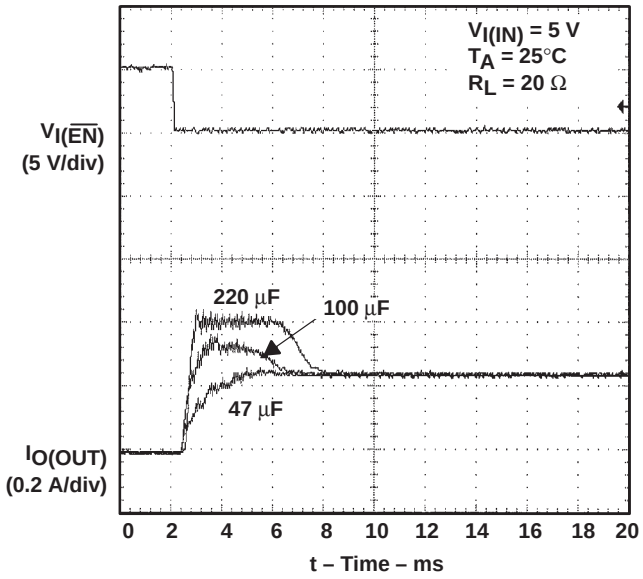


Figure 8. Inrush Current with 220-μF, 100-μF and 47-μF Load Capacitance

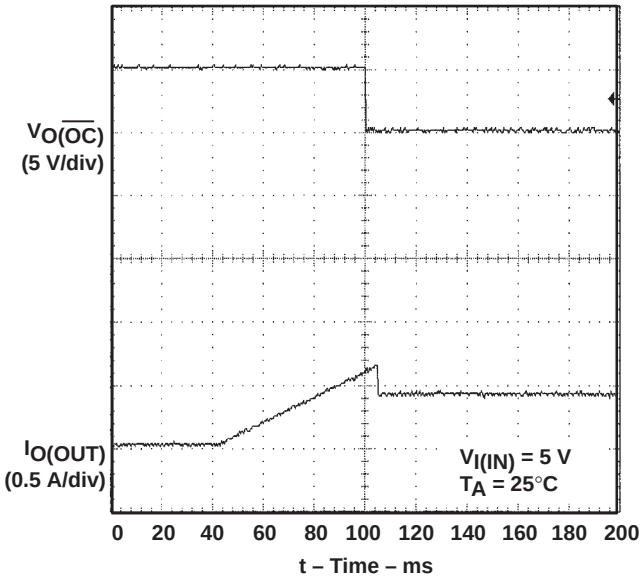


Figure 9. Ramped Load on Enabled Device

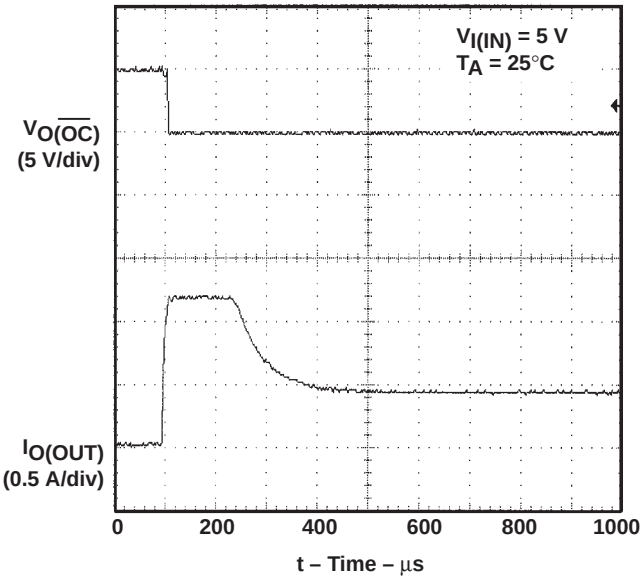


Figure 10. 4-Ω Load Connected to Enabled Device

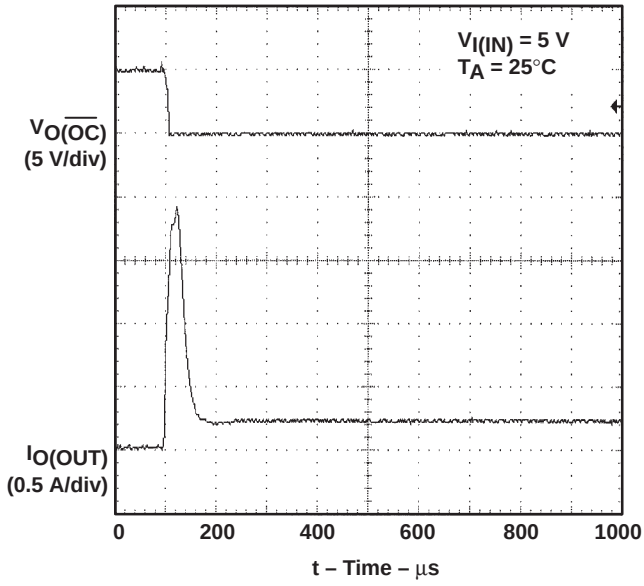


Figure 11. 1-Ω Load Connected to Enabled Device

TYPICAL CHARACTERISTICS

TURNON DELAY vs INPUT VOLTAGE

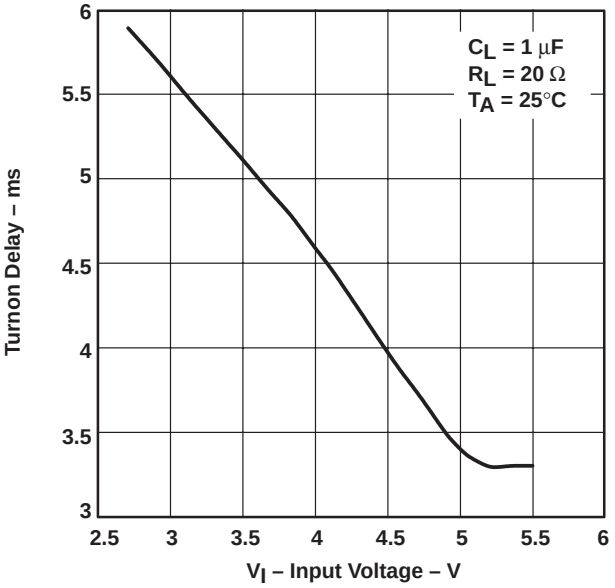


Figure 12

TURNOFF DELAY vs INPUT VOLTAGE

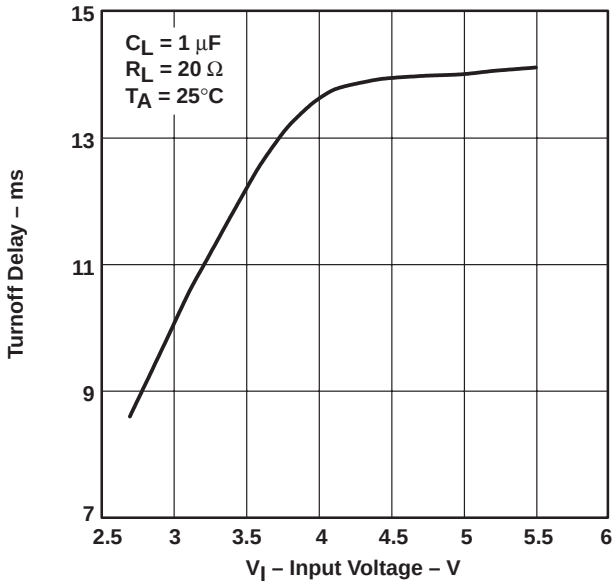


Figure 13

RISE TIME vs LOAD CURRENT

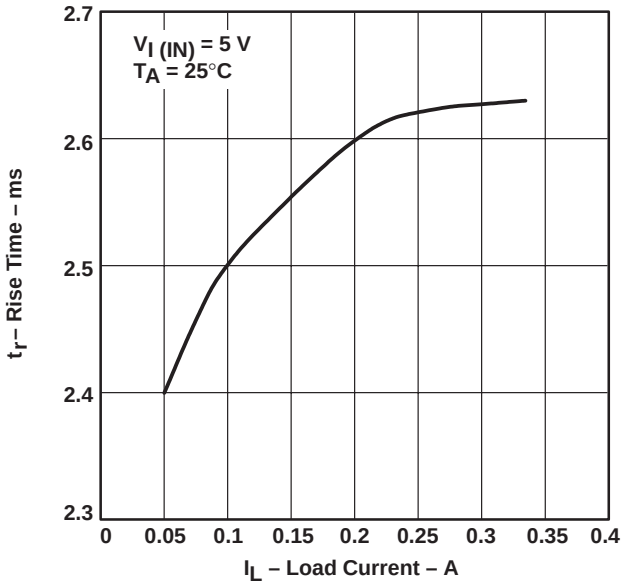


Figure 14

FALL TIME vs LOAD CURRENT

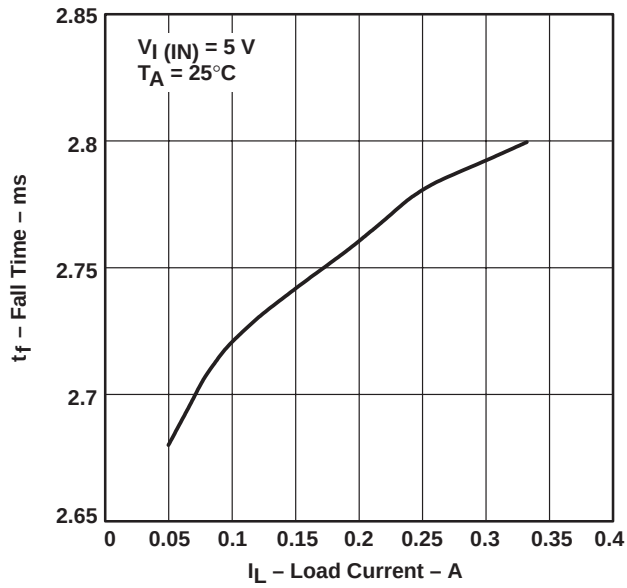


Figure 15

TYPICAL CHARACTERISTICS

SUPPLY CURRENT, OUTPUT ENABLED vs JUNCTION TEMPERATURE

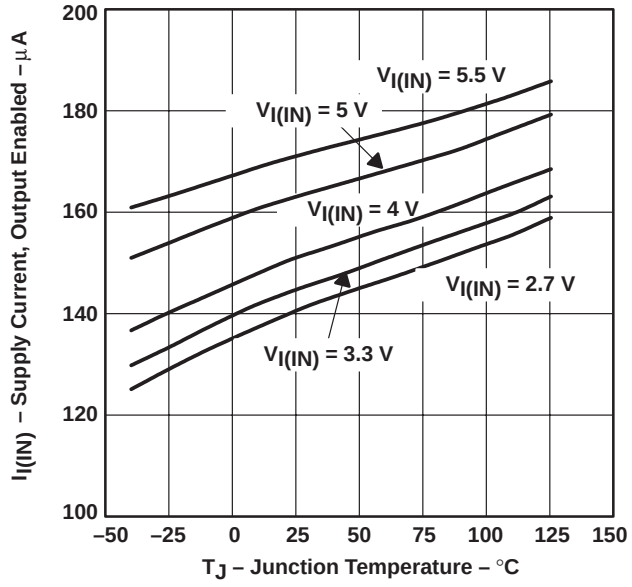


Figure 16

SUPPLY CURRENT, OUTPUT DISABLED vs JUNCTION TEMPERATURE

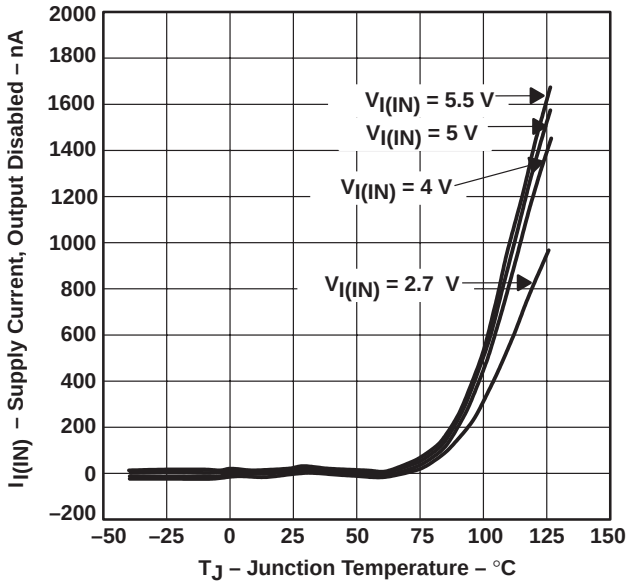


Figure 17

SUPPLY CURRENT, OUTPUT ENABLED vs INPUT VOLTAGE

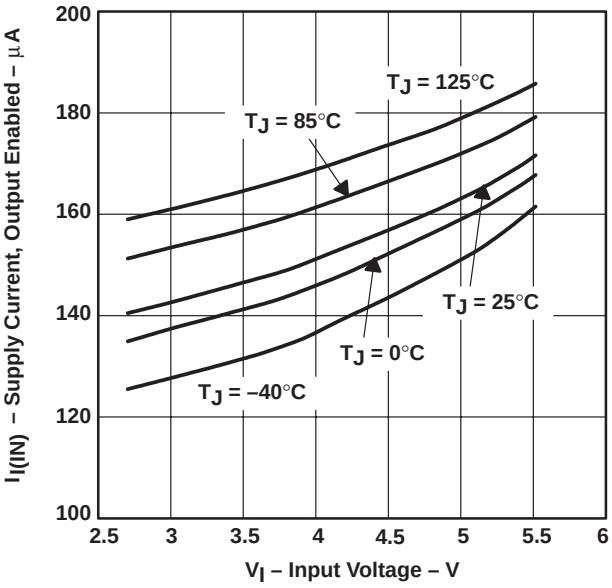


Figure 18

SUPPLY CURRENT, OUTPUT DISABLED vs INPUT VOLTAGE

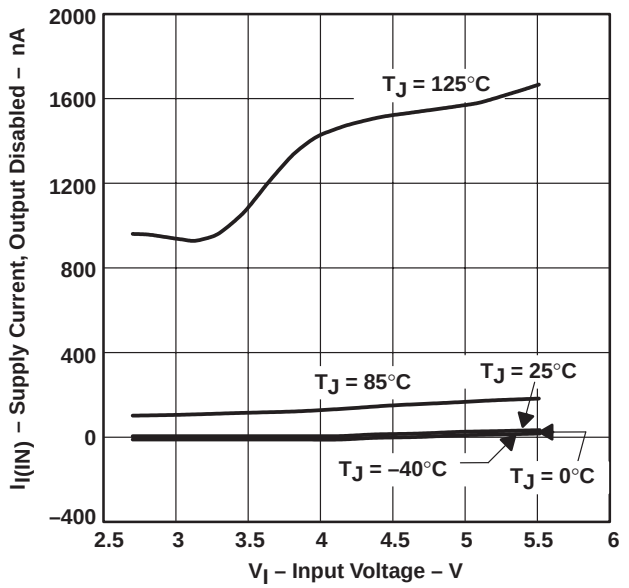


Figure 19

TYPICAL CHARACTERISTICS

STATIC DRAIN-SOURCE ON-STATE RESISTANCE vs JUNCTION TEMPERATURE

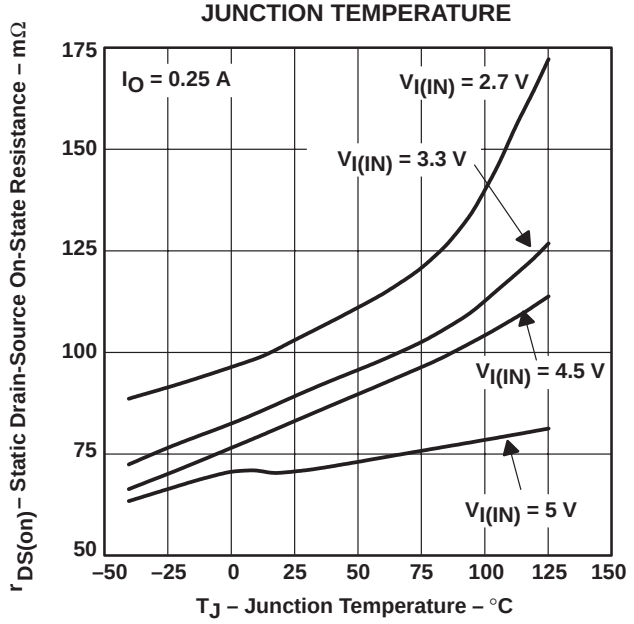


Figure 20

STATIC DRAIN-SOURCE ON-STATE RESISTANCE vs INPUT VOLTAGE

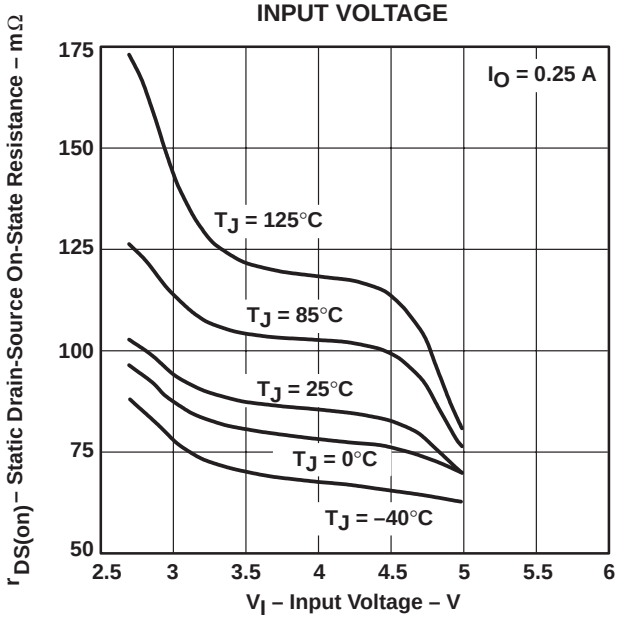


Figure 21

INPUT-TO-OUTPUT VOLTAGE vs LOAD CURRENT

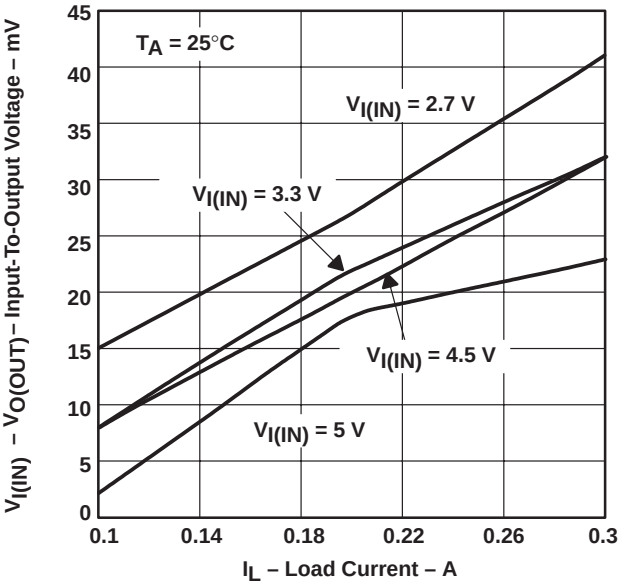


Figure 22

SHORT-CURCUIT OUTPUT CURRENT vs INPUT VOLTAGE

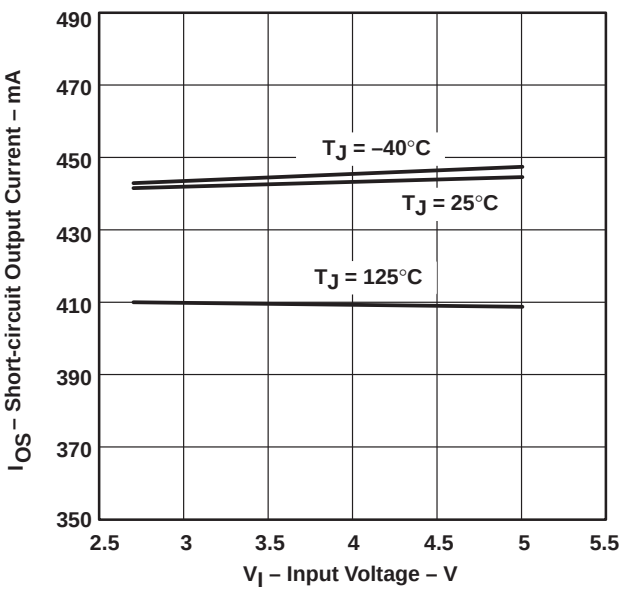


Figure 23

TYPICAL CHARACTERISTICS

THRESHOLD TRIP CURRENT
vs
INPUT VOLTAGE

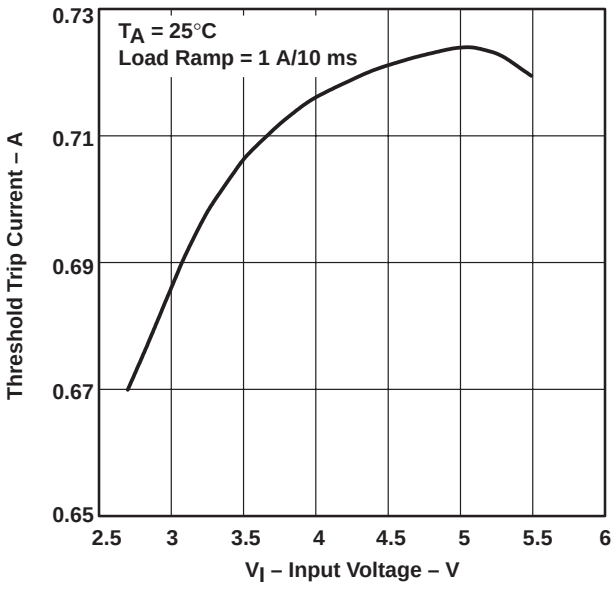


Figure 24

SHORTCIRCUIT OUTPUT CURRENT
vs
JUNCTION TEMPERATURE

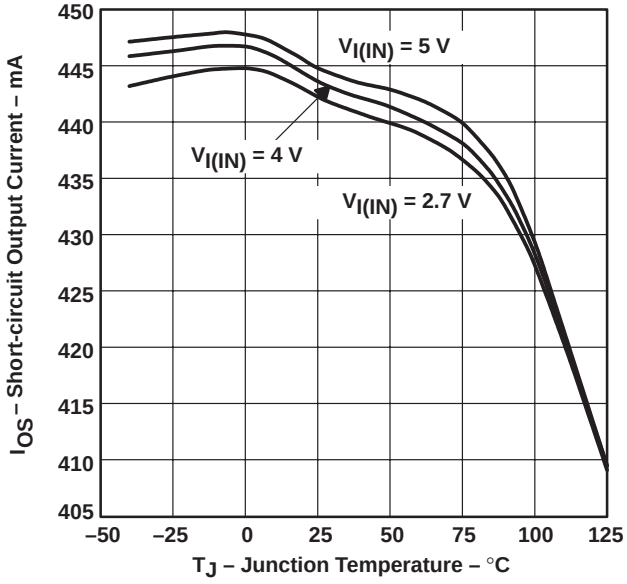


Figure 25

UNDERVOLTAGE LOCKOUT
vs
JUNCTION TEMPERATURE

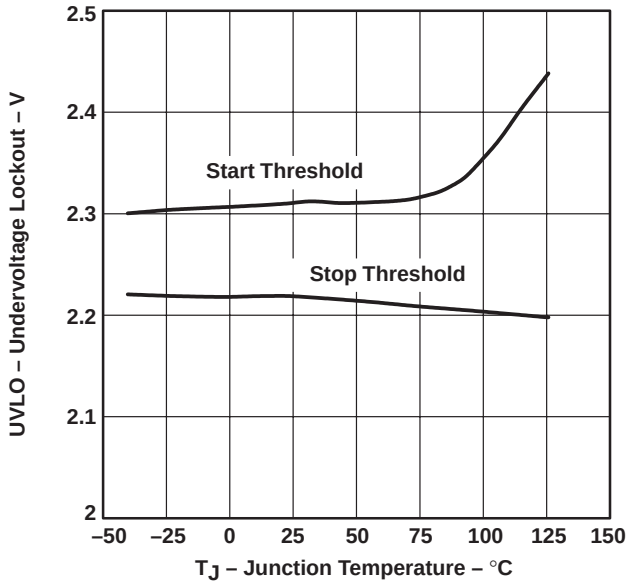


Figure 26

CURRENT-LIMIT RESPONSE
vs
PEAK CURRENT

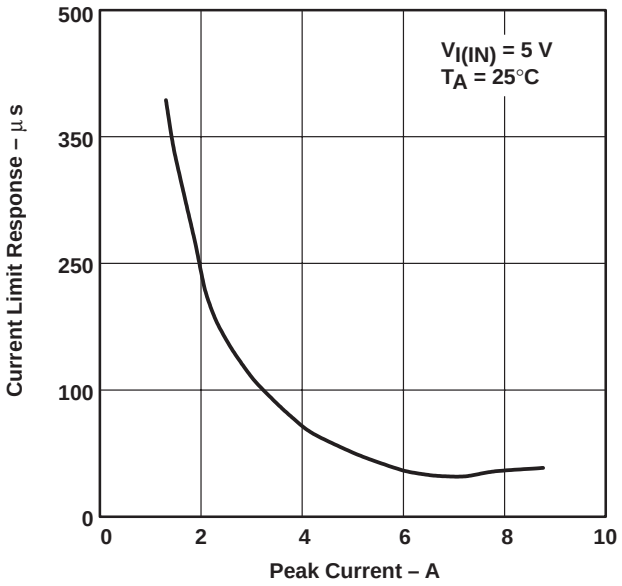


Figure 27

TYPICAL CHARACTERISTICS

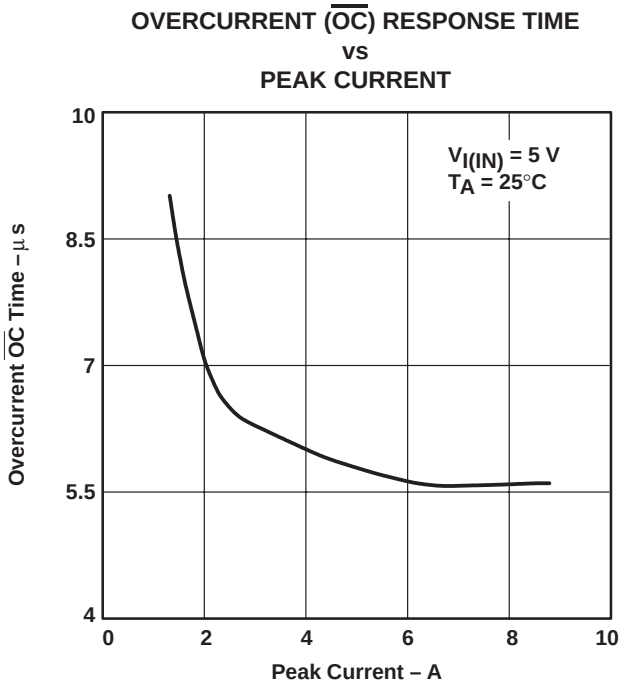


Figure 28

APPLICATION INFORMATION

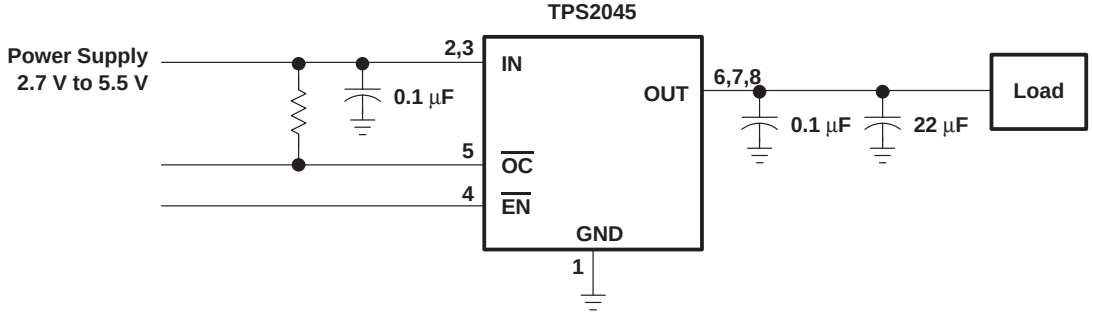


Figure 29. Typical Application

power-supply considerations

A 0.01-µF to 0.1-µF ceramic bypass capacitor between IN and GND, close to the device, is recommended. Placing a high-value electrolytic capacitor on the output pin(s) is recommended when the output load is heavy. This precaution reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the output with a 0.01-µF to 0.1-µF ceramic capacitor improves the immunity of the device to short-circuit transients.

APPLICATION INFORMATION

overcurrent

A sense FET is employed to check for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the device maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault is present long enough to activate thermal limiting.

Three possible overload conditions can occur. In the first condition, the output has been shorted before the device is enabled or before $V_{I(IN)}$ has been applied (see Figure 6). The TPS2045 and TPS2055 sense the short and immediately switch into a constant-current output.

In the second condition, the short occurs while the device is enabled. At the instant the short occurs, very high currents may flow for a short time before the current-limit circuit can react. After the current-limit circuit has tripped (reached the overcurrent trip threshhold) the device switches into constant-current mode.

In the third condition, the load has been gradually increased beyond the recommended operating current. The current is permitted to rise until the current-limit threshold is reached or until the thermal limit of the device is exceeded (see Figure 7). The TPS2045 and TPS2055 are capable of delivering current up to the current-limit threshold without damaging the device. Once the threshold has been reached, the device switches into its constant-current mode.

$\overline{OC}$ response

The $\overline{OC}$ open-drain output is asserted (active low) when an overcurrent or overtemperature condition is encountered. The output will remain asserted until the overcurrent or overtemperature condition is removed. Connecting a heavy capacitive load to an enabled device can cause momentary false overcurrent reporting from the inrush current flowing through the device, charging the downstream capacitor. An RC filter of 500 μs (see Figure 30) can be connected to the $\overline{OC}$ pin to reduce false overcurrent reporting caused by hot-plug switching events or extremely high capacitive loads. Using low-ESR electrolytic capacitors on the output lowers the inrush current flow through the device during hot-plug events by providing a low impedance energy source, thereby reducing erroneous overcurrent reporting.

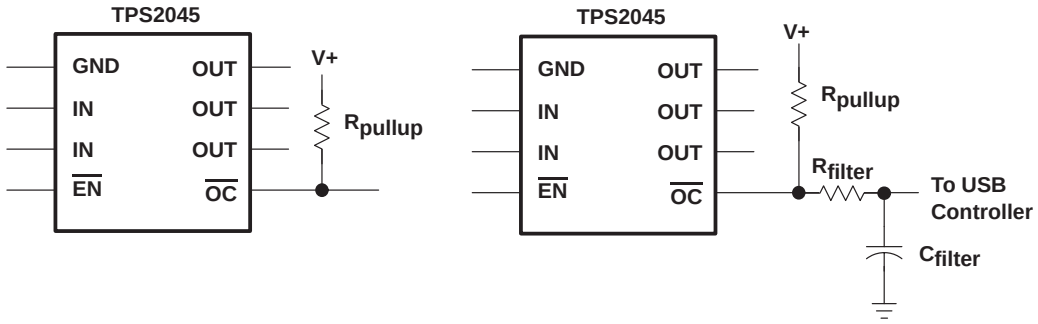


Figure 30. Typical Circuit for $\overline{OC}$ Pin and RC Filter for Damping Inrush $\overline{OC}$ Responses

APPLICATION INFORMATION

power dissipation and junction temperature

The low on-resistance on the n-channel MOSFET allows small surface-mount packages, such as SOIC, to pass large currents. The thermal resistances of these packages are high compared to those of power packages; it is good design practice to check power dissipation and junction temperature. The first step is to find $r_{DS(on)}$ at the input voltage and operating temperature. As an initial estimate, use the highest operating ambient temperature of interest and read $r_{DS(on)}$ from Figure 21. Next, calculate the power dissipation using:

$$P_D = r_{DS(on)} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times R_{\theta JA} + T_A$$

Where:

T_A = Ambient Temperature °C
$R_{\theta JA}$ = Thermal resistance SOIC = 172°C/W, PDIP = 106°C/W

Compare the calculated junction temperature with the initial estimate. If they do not agree within a few degrees, repeat the calculation, using the calculated value as the new estimate. Two or three iterations are generally sufficient to get a reasonable answer.

thermal protection

Thermal protection prevents damage to the IC when heavy-overload or short-circuit faults are present for extended periods of time. The faults force the TPS2045 and TPS2055 into constant current mode, which causes the voltage across the high-side switch to increase; under short-circuit conditions, the voltage across the switch is equal to the input voltage. The increased dissipation causes the junction temperature to rise to high levels. The protection circuit senses the junction temperature of the switch and shuts it off. Hysteresis is built into the thermal sense circuit, and after the device has cooled approximately 20 degrees, the switch turns back on. The switch continues to cycle in this manner until the load fault or input power is removed.

undervoltage lockout (UVLO)

An undervoltage lockout ensures that the power switch is in the off state at power up. Whenever the input voltage falls below approximately 2 V, the power switch will be quickly turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed. The UVLO will also keep the switch from being turned on until the power supply has reached at least 2 V, even if the switch is enabled. Upon reinsertion, the power switch will be turned on, with a controlled rise time to reduce EMI and voltage overshoots.

APPLICATION INFORMATION

Universal Serial Bus (USB) applications

The Universal Serial Bus (USB) interface is a 12-Mb/s, or 1.5-Mb/s, multiplexed serial bus designed for low-to-medium bandwidth PC peripherals (e.g., keyboards, printers, scanners, and mice). The four-wire USB interface is conceived for dynamic attach-detach (hot plug-unplug) of peripherals. Two lines are provided for differential data, and two lines are provided for 5-V power distribution.

USB data is a 3.3-V level signal, but power is distributed at 5 V to allow for voltage drops in cases where power is distributed through more than one hub across long cables. Each function must provide its own regulated 3.3 V from the 5-V input or its own internal power supply.

The USB specification defines the following five classes of devices, each differentiated by power-consumption requirements:

- Hosts/self-powered hubs (SPH)
- Bus-powered hubs (BPH)
- Low-power, bus-powered functions
- High-power, bus-powered functions
- Self-powered functions

Self-powered and bus-powered hubs distribute data and power to downstream functions. The TPS2045 and TPS2055 can provide power-distribution solutions for many of these classes of devices.

Bus-powered hubs obtain all power from upstream ports and often contain an embedded function. The hubs are required to power up with less than one unit load. The BPH usually has one embedded function, and power is always available to the controller of the hub. If the embedded function and hub require more than 100 mA on power up, the power to the embedded function may need to be kept off until enumeration is completed. This can be accomplished by removing power or by shutting off the clock to the embedded function. Power switching the embedded function is not necessary if the aggregate power draw for the function and controller is less than one unit load. The total current drawn by the bus-powered device is the sum of the current to the controller, the embedded function, and the downstream ports, and it is limited to 500 mA from an upstream port.

low-power bus-powered functions and high-power bus-powered functions

Both low-power and high-power bus-powered functions obtain all power from upstream ports; low-power functions always draw less than 100 mA; high-power functions must draw less than 100 mA at power up and can draw up to 500 mA after enumeration. If the load of the function is more than the parallel combination of 44 Ω and 10 μF at power up, the device must implement inrush current limiting (see Figure 31).

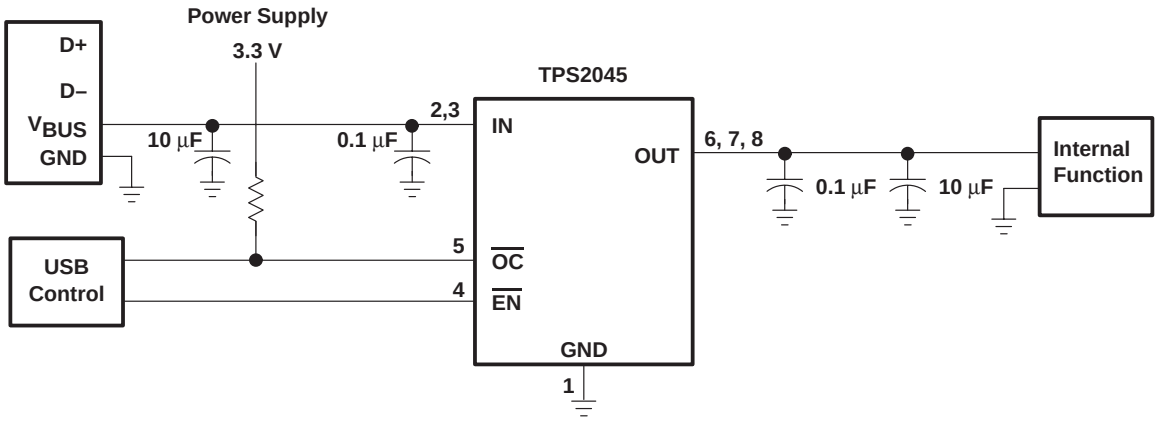


Figure 31. High-Power Bus-Powered Function

APPLICATION INFORMATION

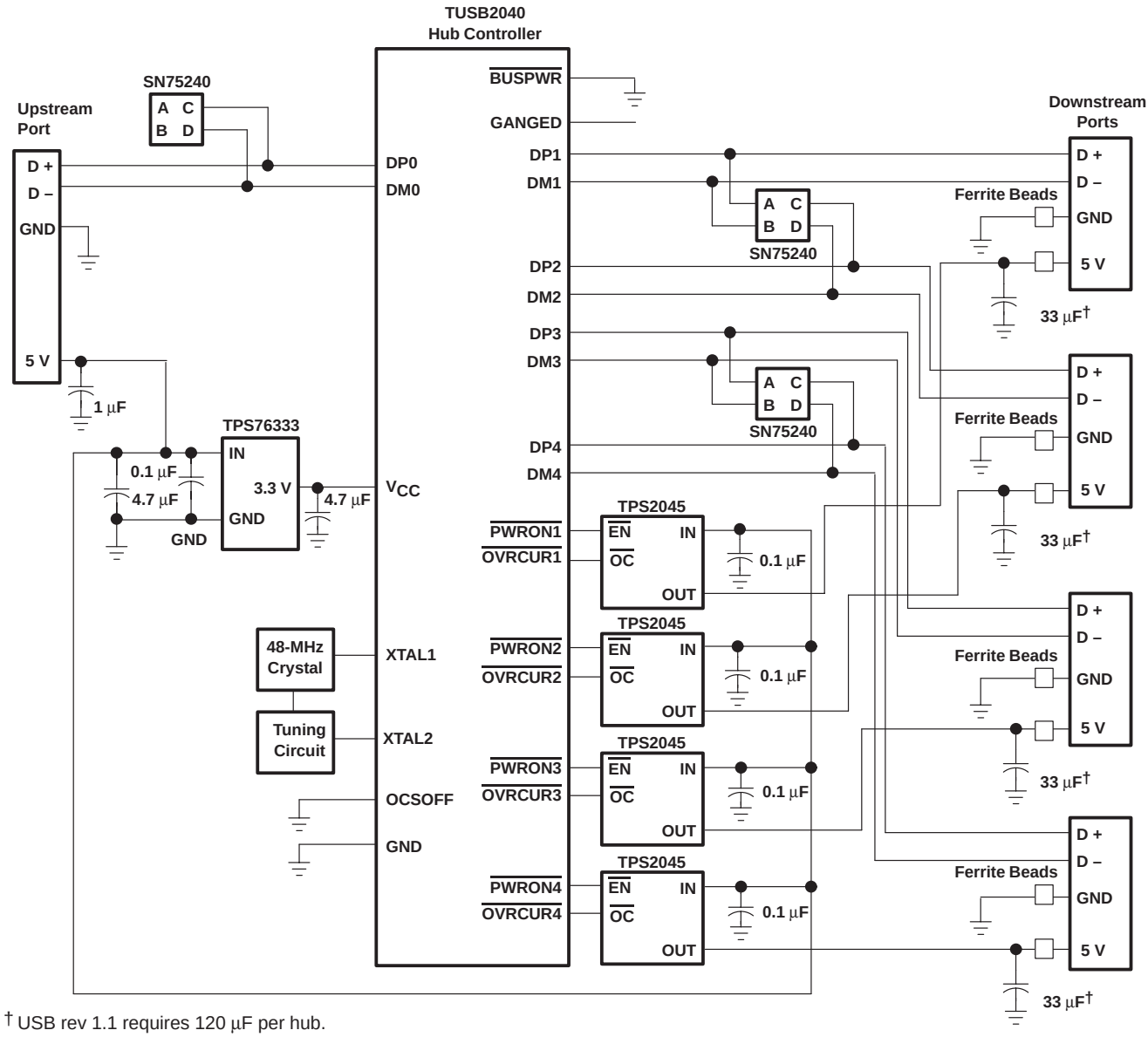
USB power-distribution requirements

USB can be implemented in several ways, and, regardless of the type of USB device being developed, several power distribution features must be implemented.

- Bus-Powered Hubs must:
  - Enable/disable power to downstream ports
  - Power up at <100 mA
  - Limit inrush current (<44 Ω and 10 μF)
- Functions must:
  - Limit inrush currents
  - Power up at <100 mA

The feature set of the TPS2045 and TPS2055 allows them to meet each of these requirements. The integrated current-limiting and overcurrent reporting is required by hosts and self-powered hubs. The logic-level enable and controlled rise times meet the need of both input and output ports on bus-power hubs, as well as the input ports for bus-power functions (see Figure 32).

APPLICATION INFORMATION



† USB rev 1.1 requires 120 μF per hub.

Figure 32. Bus-Powered Hub Implementation

APPLICATION INFORMATION

generic hot-plug applications (see Figure 33)

In many applications it may be necessary to remove modules or pc boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise times and fall times of the TPS2045 and TPS2055, these devices can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the TPS2045 and TPS2055 also ensures the switch will be off after the card has been removed, and the switch will be off during the next insertion. The UVLO feature guarantees a soft start with a controlled rise time for every insertion of the card or module.

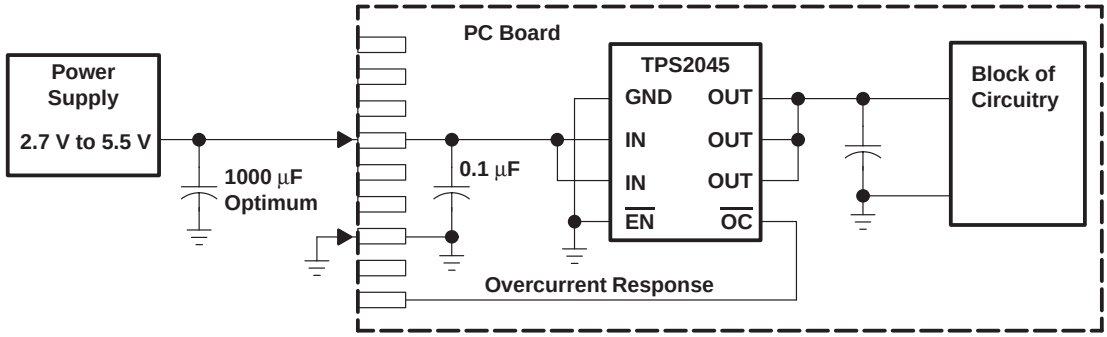


Figure 33. Typical Hot-Plug Implementation

By placing the TPS2045 and TPS2055 between the V_{CC} input and the rest of the circuitry, the input power will reach these devices first after insertion. The typical rise time of the switch is approximately 2.5 ms, providng a slow voltage ramp at the output of the device. This implementaion controls system surge currents and provides a hot-plugging mechanism for any device.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS2045D	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2045
TPS2045D.A	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2045
TPS2045DR	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2045
TPS2045DR.A	Active	Production	SOIC (D) | 8	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2045
TPS2055D	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2055
TPS2055D.A	Active	Production	SOIC (D) | 8	75 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2055

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

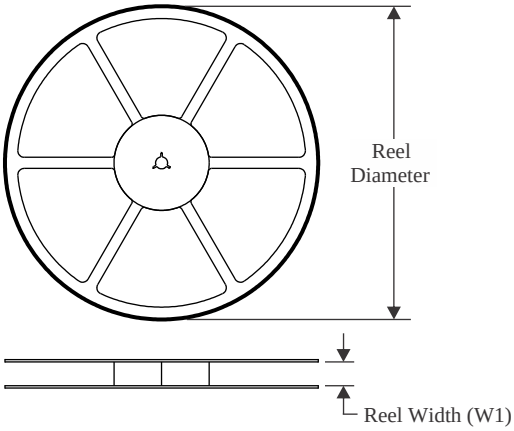
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

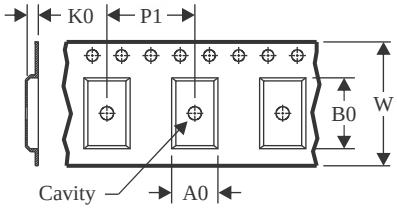
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

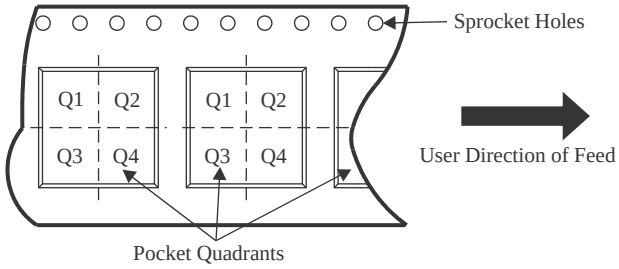


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

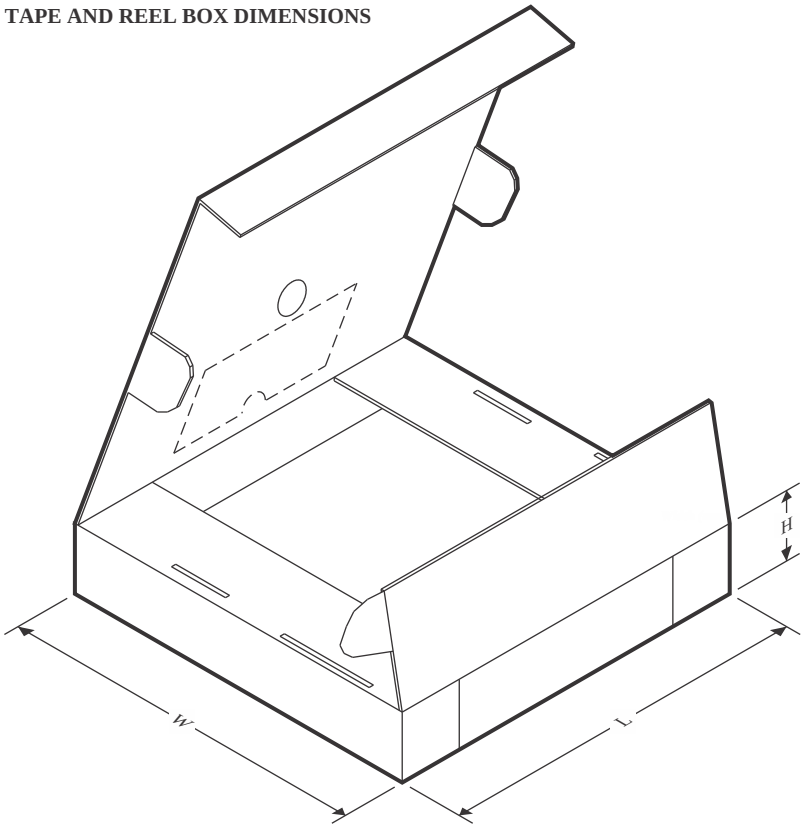
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2045DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

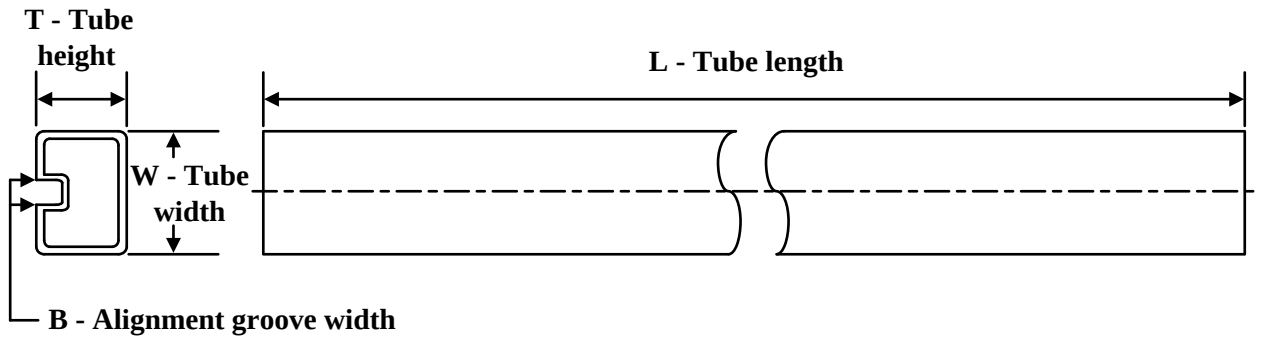
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2045DR	SOIC	D	8	2500	353.0	353.0	32.0

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
TPS2045D	D	SOIC	8	75	507	8	3940	4.32
TPS2045D.A	D	SOIC	8	75	507	8	3940	4.32
TPS2055D	D	SOIC	8	75	507	8	3940	4.32
TPS2055D.A	D	SOIC	8	75	507	8	3940	4.32

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